

CLAIM AMENDMENTS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-3 (previously canceled).

4 (previously presented). A process for metallizing at least one insulating layer of an electronic or microelectronic component, which comprises:

applying at least one first insulating layer to a substrate such that the first insulating layer has a thickness not greater than 50 m;

activating the entire first insulating layer by treatment with an activator, the activator being at least one of a gas, a liquid, a solution, and a plasma;

then, after activating the entire first insulating layer, applying and patterning a second insulating layer made of a photosensitive material; and

then, after applying and patterning the second insulating layer, seeding and metallizing regions of the first insulating layer that are exposed by the patterning step.

5 (previously presented). The process according to claim 4, which comprises forming the first insulating layer and the second insulating layer from the same material.

6 (currently amended). The process according to claim 5, which comprises patterning the first insulating layer before the entire first layer is activated and before the second insulating layer is applied.

7 (currently amended). The process according to claim 4, which comprises patterning the first insulating layer before the entire first layer is activated and before the second insulating layer is applied.